

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

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Applicants: Jack H. Yuan, Eliyahou Harari, Yupin K. Fong and George Samachisa
Title: Scalable Self-Aligned Dual Floating Gate Memory Cell Array and Methods of Forming the Array

Application No.:	10/799,180	Filing Date:	March 12, 2004
Examiner:	Igwe U. Anya	Group Art Unit:	2812
Docket No.:	SNDK.257US2	Conf. No.:	8152

Mail Stop Amendment
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

Dear Sir:

Pursuant to 37 C.F.R. §§ 1.56, 1.97 and 1.98, Applicants call the documents listed on the enclosed Form PTO-1449 to the Examiner's attention in this patent application.

This application has a filing date after June 30, 2003. Copies of the U.S. Patent(s) and U.S. Published Patent Application(s) documents listed on the accompanying Form PTO-1449 are not enclosed.

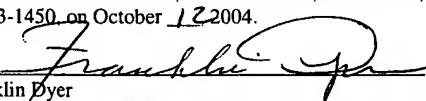
Citation of these documents shall not be construed as (1) an admission that the documents are prior art with respect to the invention or inventions claimed in this application, (2) a representation that a search has been made (other than as indicated by any cited document), or (3) an admission that the cited information is, or is considered to be, material to patentability as defined in § 1.56(b).

This information disclosure statement is submitted under 37 C.F.R. § 1.97(c). A check including \$180.00 for the information disclosure statement fee under 37 C.F.R. § 1.17(p), is

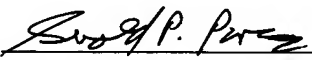
Attorney Docket No.: SNDK.257US2

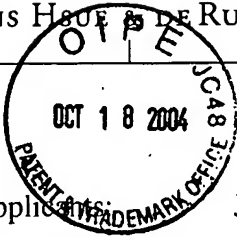
Application No.: 10/799,180

enclosed. The Commissioner is authorized, however, to charge any fee that may be required, or to credit any overpayment, against Deposit Account No. 502664. This form is being submitted in duplicate.

<p align="center"><u>Certificate of Mailing Under 37 CFR 1.8</u></p> <p>I hereby certify that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail in an envelope address to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450 on October <u>12</u> 2004.</p> <p> _____ Franklin Dyer</p>
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Respectfully submitted,

	<u>10/12/04</u>
Gerald P. Parsons	Date
Reg. No. 24,486	



655 Montgomery Street, Suite 1800 San Francisco, Ca 94111
tel 415.318.1160 fax 415.693.0194

Applicant: Jack H. Yuan, Eliyahou Harari, Yupin K. Fong and George Samachisa

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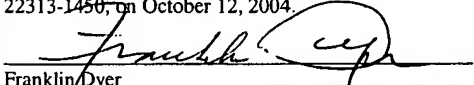
Dear Sir:

Transmitted herewith are the following documents in the above-identified application:


- (1) Return receipt postcard;
- (2) This Transmittal Letter (1 page – in duplicate);
- (3) Amendment (8 pages);
- (4) Information Disclosure Statement (2 pages);
- (5) PTO Form 1449 (3 sheets);
- (6) 3 Cited References; and
- (7) Check for \$180.00.

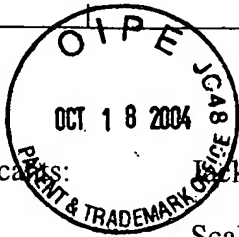
☒ Conditional Petition for Extension of Time: If an extension of time is required for timely filing of the enclosed document(s) after all papers filed with this transmittal have been considered, an extension of time is hereby requested.

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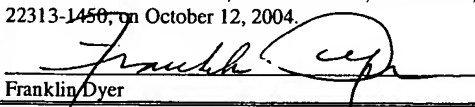
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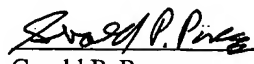
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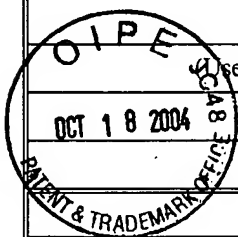
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U.S. Department of Commerce, Patent and Trademark	Atty. Docket No.	Application No.
INFORMATION DISCLOSURE STATEMENT BY APPLICANT	SN DK.257US2	10/799,180
	Applicant(s)	Conf. No.
(Use several sheets if necessary)	Jack H. Yuan et al.	8152
	Filing Date	Group
	March 12, 2002	2812



U.S. Patent Documents

*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
	1	5,168,465	12/1992	Harari			
	2	5,198,380	3/1993	Harari			
	3	5,268,318	12/1993	Harari			
	4	5,268,319	12/1993	Harari			
	5	5,279,982	1/1994	Crotti			
	6	5,380,672	1/1995	Yuan et al.			
	7	5,512,505	4/1996	Yuan et al.			
	8	5,534,456	7/1996	Yuan et al.			
	9	5,554,553	9/1996	Harai			
	10	5,579,259	11/1996	Samachisa et al.			
	11	5,595,924	1/1997	Yuan et al.			
	12	5,640,032	6/1997	Tomioka			
	13	5,654,217	8/1997	Yuan et al.			
	14	5,661,053	8/1997	Yuan			
	15	5,677,872	10/1997	Samachisa			
	16	5,712,179	1/1998	Yuan			
	17	5,747,359	5/1998	Yuan			
	18	5,756,385	5.1998	Yuan			
	19	5,786,988	7/1998	Harari			
	20	5,847,425	12/1998	Yuan			
	21	5,867,429	2/1999	Chen			
	22	5,883,409	3/1999	Guterman			
	23	5,923,976	7/1999	Kim			
	24	5,965,913	10/1999	Yuan			
	25	5,981,335	11/1999	Chi			
	26	5,999,448	12/1999	Kurihara			

Examiner

Date Considered

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with your communication to applicant.

[illegible]

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				March 12, 2002		2812		
U.S. Published Patent Application Documents								
*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate	
	42	US2001/0001491	5/24/2001	Sakui				
	43	US2002/0093073	07/18/02	Mori et al.				
Foreign Patent Documents								
							Translation	
		Document	Date	Country	Class	Subclass	Yes	No
	44	2002/0088554	11/29/2002	Korea			X	
OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)								
	45	Aritome et al., "A Novel Side-Wall Transfer-Transistor Cell (SWATT Cell) For Multi-Level NAND EEPROMs", 1995 IEEE International Solid-State Circuits Conference, IEDM 95, pp. 275-8.						
	46	Aritome et al., "A0.67um ² Self-Aligned Shallow Trench Isolation Cell (SA-STI CELL) for 3V-only 256Mbit NAND EEPROMs", IEDM Technical digest, pp. 61-64 (1994).						
	47	Cho et al., "A Dual-Mode NAND Flash Memory: 1-Gb Multilevel and High-Performance 512-Mb Single-Level Modes", IEEE Journal of Solid-State Circuits, Vol. 36, No. 11, pp. 1700-1706 (2001).						
Examiner			Date Considered					
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